



IPee

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Chikako YOSHIDA et al.

Group Art Unit: 2811

Serial No.: 10/768,090

Examiner: TBA

Filed: February 2, 2004

Confirmation No.: 5757

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE
SAME

Attorney Docket No.: 042071
Customer Number: 38834

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

June 15, 2004

Sir:

Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached Form PTO-1449. A copy of each document listed, is attached.

No fee or certification is required in connection with this Information Disclosure Statement, because it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following the filing date or the entry of the national stage of the above-captioned application.

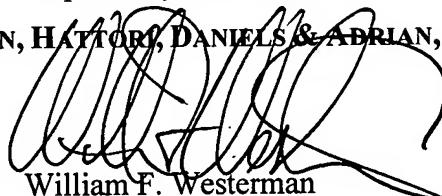
The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. Applicants respectfully request that the information be expressly considered during the prosecution of this application and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

Appln. Serial No. 10/768,090
By: Chikako YOSHIDA et al.

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee
that is required to effect consideration of this statement.

Respectfully submitted,

WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP



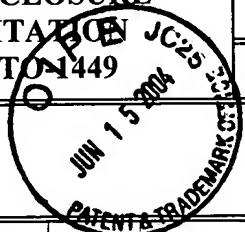
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Enclosures: PTO-1449 Form
(8) References

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 042071	Serial No. 10/768,090
Applicant(s): Chikako YOSHIDA et al.		
	Filing Date: February 2, 2004	Group Art Unit: 2811



U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
	WO 03/014830 A1	2/20/03	WIPO	
	11307549 A	11/5/99	Japan	Yes
	10073927	3/17/98	Japan	Yes
	08115923 A	5/7/96	Japan	Yes
	07153666 A	6/16/95	Japan	Yes
	2002-033320 A	1/31/02	Japan	Yes
	2001-267566	9/28/01	Japan	Yes

OTHER DOCUMENTS

		D.C. Gilmer et al., "Compatibility of Polycrystalline Silicon Gate Deposition with HfO ₂ and Al ₂ O ₃ /HfO ₂ gate dielectrics", Appl. Phys. Lett., Vol. 81, No. 7, pp. 1288-1290.
Examiner		Date Considered